

REMARKS/ARGUMENTS

Claims 3 and 24 were objected to for informalities. Claims 1 to 2, 4 to 5, 7 to 14, 16 to 18, and 21 to 22 were rejected under 35 U.S.C. § 102 (b) as being anticipated by Hess (WO 00/21753 and US 2002/0035938). Claims 6, 10 and 15 were rejected under 35 U.S.C. § 103 (a) as being unpatentable over Hess. Claims 3, 19, 20, 23, and 24 were rejected under 35 U.S.C. § 103 (a) as being unpatentable over Hess in view of Kobayashi et al. (US 6,294,313).

Claims 3 and 24 have been amended to correct the informalities, and claims 1, 11 and 25 also amended.

Reconsideration of the application is respectfully requested.

Claim Objections

Claims 3 and 24 were objected to for informalities. Claims 3 and 24 have been amended to correct the informalities. Withdrawal of the objections is respectfully requested.

35 U.S.C. 102 Rejections

Claims 1 to 2, 4 to 5, 7 to 14, 16 to 18, and 21 to 22 were rejected under 35 U.S.C. § 102 (b) as being anticipated by Hess (WO 00/21753 and US 2002/0035938).

Hess shows in Fig. 2 cited by the Office Action shows an OH group in II.

Claim 1 recites “in at least one of the hydrophobic regions, the surface having silicon atoms, at least one organic terminal group being attached to the silicon atoms of the at least one hydrophobic region in each instance, the silicon atoms being substituted not only exactly with one CH₃ group or with one OCH₃ group.”

The -OH Group cited by the Office Action is not an “organic terminal group” as it is not organic. Hess does disclose at [0052] that the -OH groups are removed and SiCH₃ or SiOCH₃ groups form. However, the silicon atoms in Fig. 2, II then are substituted with *exactly* one CH₃ group or with one OCH₃ group, and thus this disclosure also does not meet the claimed limitation of “the silicon atoms being substituted not only exactly with one CH₃ group or with one OCH₃ group.”

Advantages of such terminal groups as claimed is found for example at [0024] to [0028] for example.

Withdrawal of the rejections to claims 1 to 2, 4 to 5, 7 to 14, 16 to 18, and 21 to 22 is respectfully requested.

Claim 25 was rejected under 35 U.S.C. 102(b) as anticipated by Kobayashi.

Claim 25 has been recited to recite wherein the surface is made of amorphous, nanocrystalline, polycrystalline or crystalline silicon, or a stoichiometric or non-stoichiometric silicon ceramic containing oxygen and/or nitrogen.

Withdrawal of the rejection to claim 25 is respectfully requested.

35 U.S.C. 103 Rejections

Claims 6, 10 and 15 were rejected under 35 U.S.C. § 103 (a) as being unpatentable over Hess. Claims 3, 19, 20, 23, and 24 were rejected under 35 U.S.C. § 103 (a) as being unpatentable over Hess in view of Kobayashi et al. (US 6,294,313).

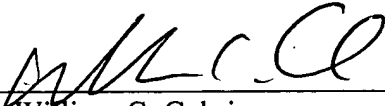
In view of the above with respect to Hess, withdrawal of the rejections is respectfully requested. In addition, it is respectfully submitted that one of skill in the art would not have used the teachings for the titanium dioxide-silicone structure of Kobayashi to use with the Hess semiconducting surface.

Withdrawal of the 103 rejections is respectfully requested.

CONCLUSION

The present application is respectfully submitted as being in condition for allowance and applicants respectfully request such action.

Respectfully submitted,
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